

DATA SHEET



BSR18A PNP switching transistor

Product specification
Supersedes data of 1997 May 28

2004 Mar 24

PNP switching transistor

BSR18A

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed saturated switching.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package.
NPN complement: BSR17A.

MARKING

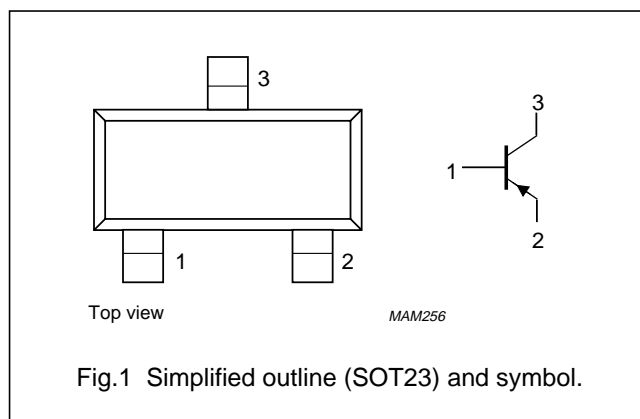
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSR18A	55* or T92

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSR18A	-	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-40	V
V _{CEO}	collector-emitter voltage	open base	-	-40	V
I _C	collector current (DC)		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	250	mW
h _{FE}	DC current gain	I _C = -10 mA; V _{CE} = -1 V	100	300	
f _T	transition frequency	I _C = -10 mA; V _{CE} = -20 V; f = 100 MHz	250	-	MHz
t _{off}	turn-off time	I _{Con} = -10 mA; I _{Bon} = -1 mA; I _{Boff} = 1 mA	-	300	ns

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

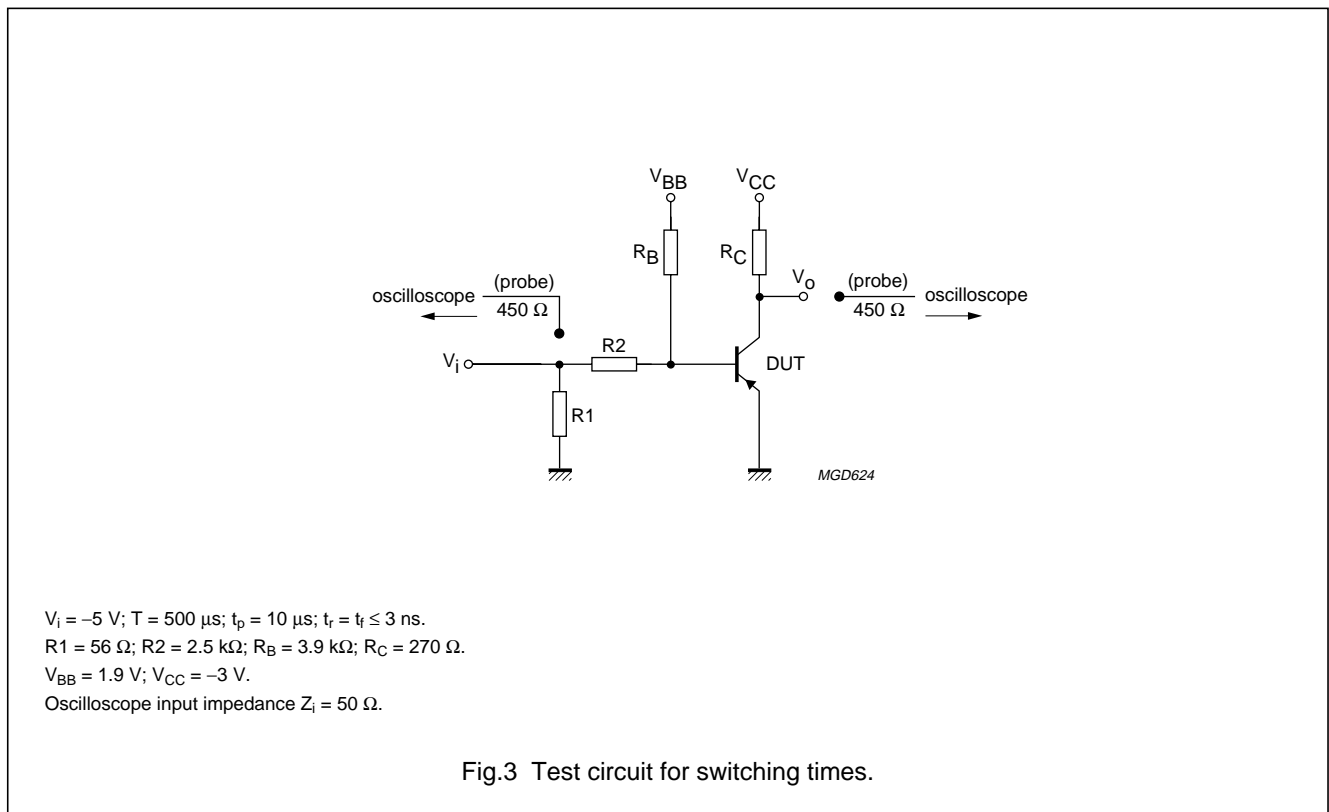
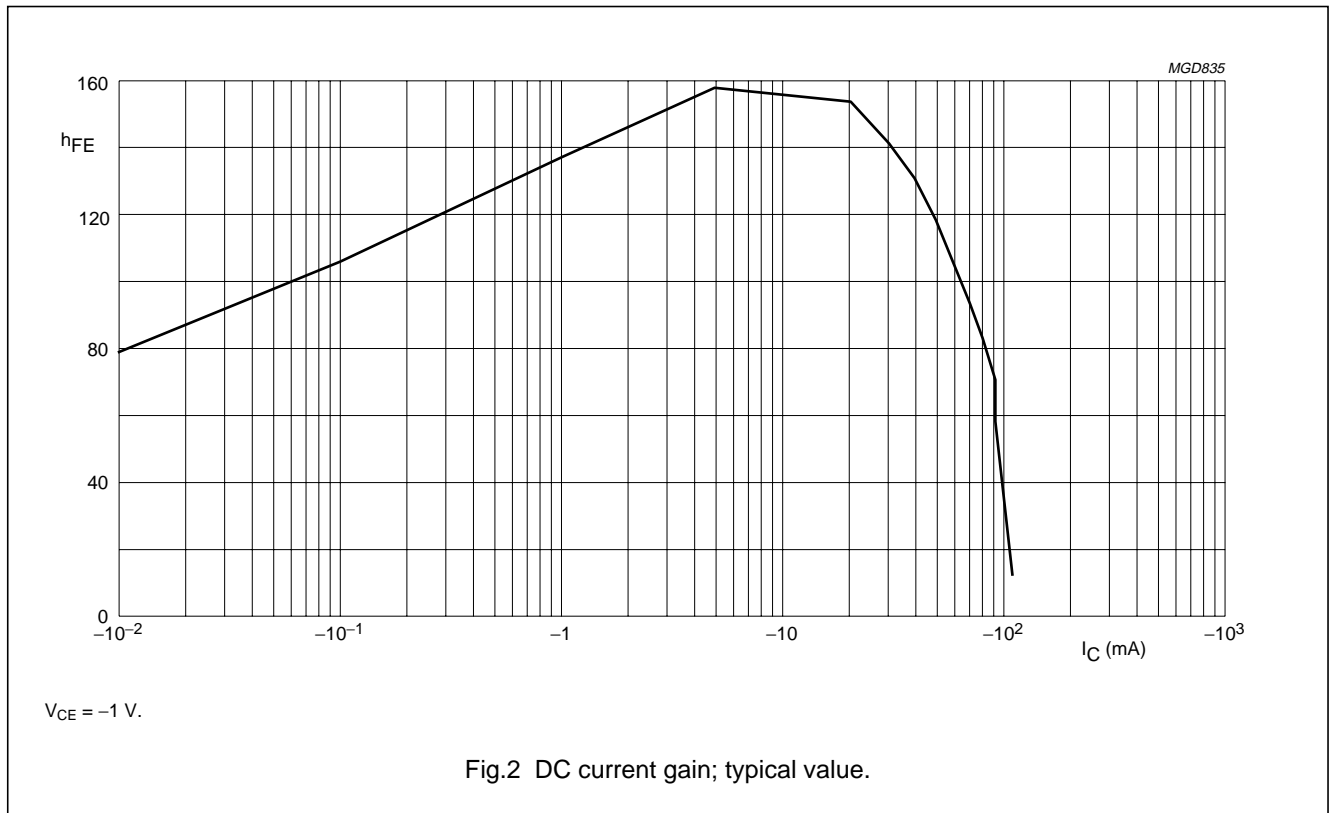
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0 A; V _{CB} = -30 V	-	-50	nA
I _{EBO}	emitter cut-off current	I _C = 0 A; V _{EB} = -6 V	-	-50	nA
h _{FE}	DC current gain	V _{CE} = -1 V; note 1; see Fig.2 I _C = -0.1 mA I _C = -1 mA I _C = -10 mA I _C = -50 mA I _C = -100 mA	60 80 100 60 30	- - 300 - -	
V _{CEsat}	collector-emitter saturation voltage	I _C = -10 mA; I _B = -1 mA; note 1	-	-200	mV
		I _C = -50 mA; I _B = -5 mA; note 1	-	-200	mV
V _{BEsat}	base-emitter saturation voltage	I _C = -10 mA; I _B = -1 mA; note 1	-650	-850	mV
		I _C = -50 mA; I _B = -5 mA; note 1	-	-950	mV
C _c	collector capacitance	I _E = i _e = 0 A; V _{CB} = -5 V; f = 1 MHz	-	4.5	pF
C _e	emitter capacitance	I _C = i _c = 0 A; V _{EB} = -500 mV; f = 1 MHz	-	10	pF
f _T	transition frequency	I _C = -10 mA; V _{CE} = -20 V; f = 100 MHz	250	-	MHz
F	noise figure	I _C = -100 μA; V _{CE} = -5 V; R _S = 1 kΩ; f = 10 Hz to 15.7 kHz	-	4	dB
Switching times (between 10% and 90% levels); see Fig.3					
t _{on}	turn-on time	I _{Con} = -10 mA; I _{Bon} = -1 mA; I _{Boff} = 1 mA	-	65	ns
t _d	delay time		-	35	ns
t _r	rise time		-	35	ns
t _{off}	turn-off time		-	300	ns
t _s	storage time		-	225	ns
t _f	fall time		-	75	ns

Note

1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.01.

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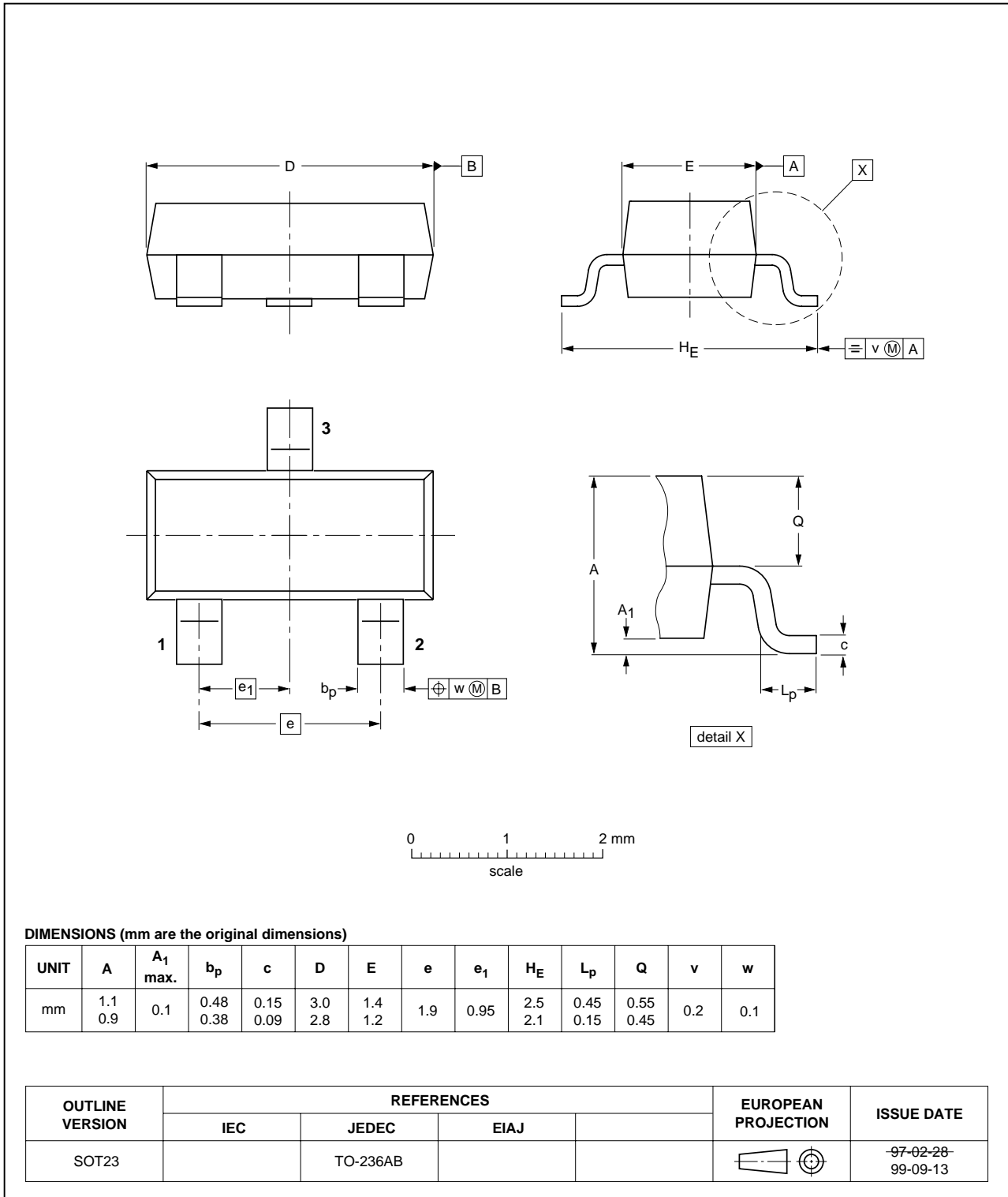
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



PNP switching transistor

BSR18A

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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